

Description

The AR3351D3 is an uni-directional TVS diode, utilizing leading monolithic silicon technology to provide fast response time and ultra low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive data and power line. The AR3351D3 complies with the IEC 61000-4-2 (ESD) with $\pm 30\text{kV}$ air and $\pm 30\text{kV}$ contact discharge. It is assembled into an ultra-small SOD-323 lead-free package. The small size and high ESD surge protection make AR3351D3 an ideal choice to protect cell phone, digital cameras, audio players and many other portable applications.

Features

- Protects one data line
- Ultra low leakage: nA level
- Operating voltage: 3.3V
- Ultra low clamping voltage
- Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
 - Air discharge: $\pm 30\text{kV}$
 - Contact discharge: $\pm 30\text{kV}$
 - IEC61000-4-5 (Lightning) 30A (8/20 μs)
- RoHS Compliant

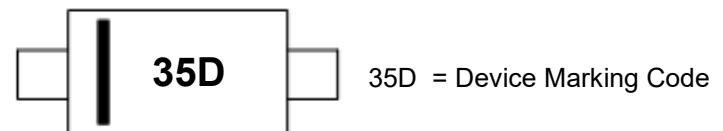
Mechanical Characteristics

- Package: SOD-323
- Case Material: “Green” Molding Compound.
- Terminal Connections: See Diagram Below
- Marking Information: See Below

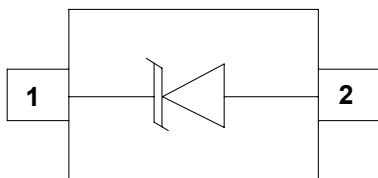
Applications

- Cellular Handsets and Accessories
- Personal Digital Assistants
- Notebooks, Desktops, Servers
- Portable Instrumentation
- Digital Cameras
- Analog Inputs
- Audio Players
- Keypads, Side Keys, LCD Displays
- Laser Diode Protection

Marking Information



Equivalent Circuit and Pin Configuration



SOD-323 (Top View)

Circuit and Pin Schematic

Ordering Information

Part Number	Packaging	Reel Size
AR3351D3	3000/Tape & Reel	7 inch

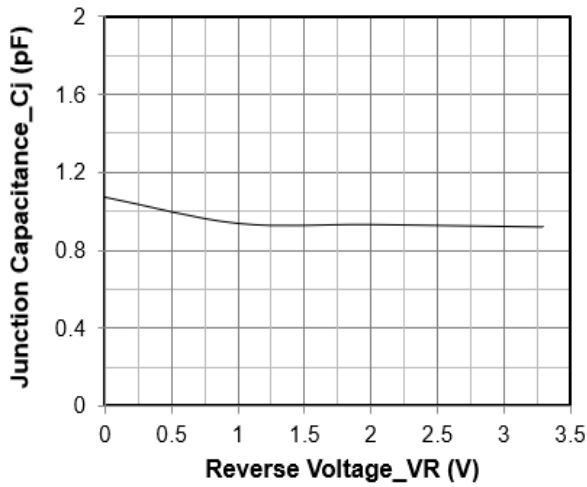
Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20 μs)	Ppk	540	W
Peak Pulse Current (8/20 μs)	Ipp	30	A
ESD per IEC 61000-4-2 (Air)	VESD	± 30	kV
ESD per IEC 61000-4-2 (Contact)		± 30	
Operating Temperature Range	TJ	-55 to +125	$^{\circ}\text{C}$
Storage Temperature Range	Tstg	-55 to +150	$^{\circ}\text{C}$

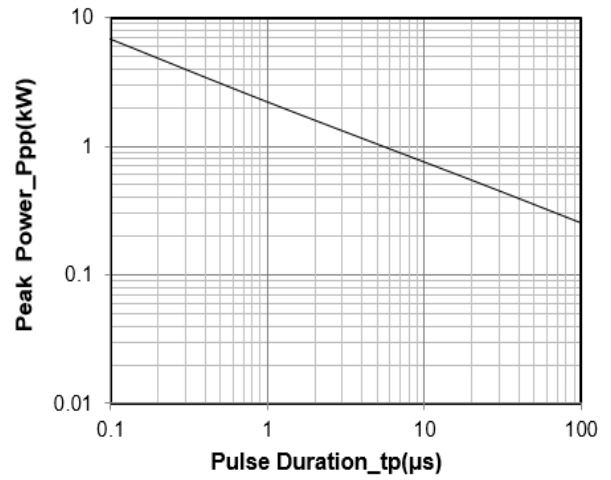
Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	VRWM			3.3	V	
Breakdown Voltage	VBR	3.5			V	IT = 1mA
Reverse Leakage Current	IR			0.2	μA	VRWM = 3.3V
Clamping Voltage	VC			7	V	I _{PP} = 1A (8 x 20 μs pulse)
Clamping Voltage	VC			18	V	I _{PP} = 30A (8 x 20 μs pulse)
Junction Capacitance	CJ		1		pF	VR = 0V, f = 1MHz

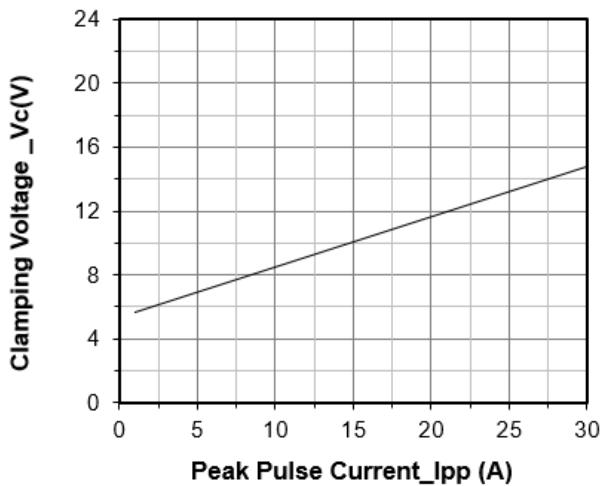
Typical Performance Characteristics ($T_A=25^\circ\text{C}$ unless otherwise Specified)



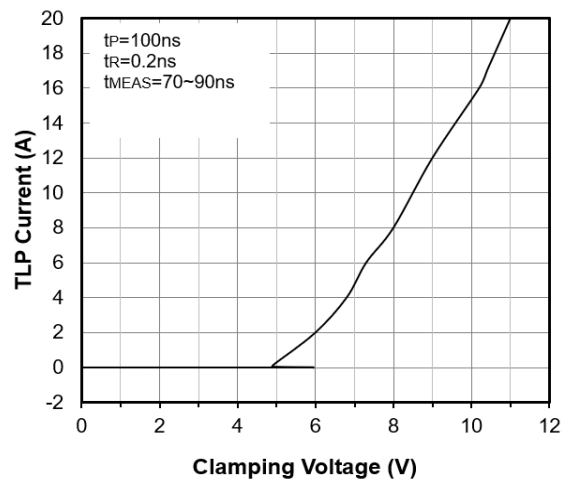
Junction Capacitance vs. Reverse Voltage



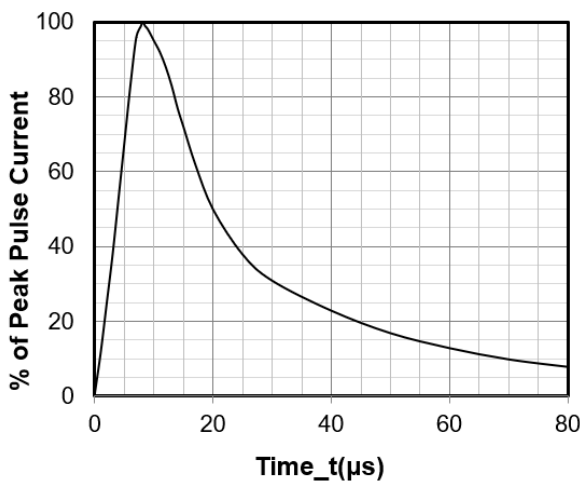
Peak Pulse Power vs. Pulse Time



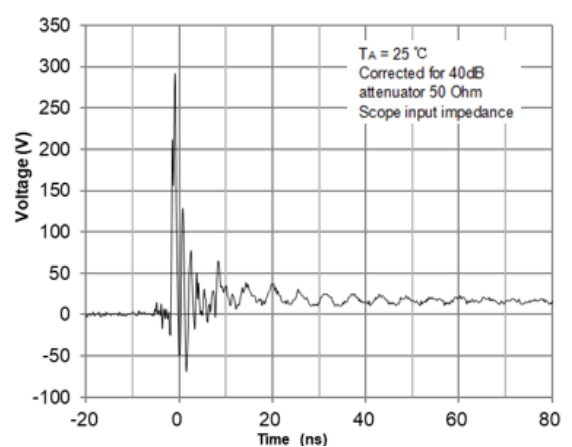
Clamping Voltage vs. Peak Pulse Current ($t_p = 8/20\mu\text{s}$)



TLP Measurement

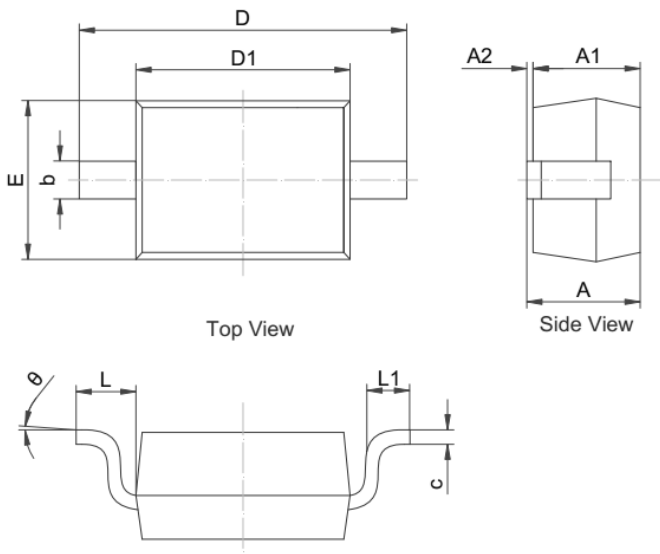


8 X 20μs Pulse Waveform



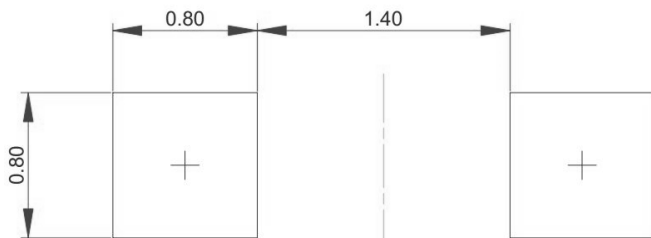
ESD Clamping Voltage
8 kV Contact per IEC61000-4-2

SOD-323 Package Outline Drawing



	MILLIMETERS		
	MIN	NOM	MAX
A	0.800	--	1.100
A1	0.800	--	0.900
A2	0.000	--	0.100
b	0.250	--	0.400
c	0.080	--	0.177
D1	1.600	1.700	1.800
D	2.300	--	2.800
E	1.150	--	1.400
L	0.475REF		
L1	0.100	--	0.500
Θ	0°	--	8°

Suggested Land Pattern



Unit: mm

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